

TECHNICAL DATA DATA SHEET 561, REV. -

704-15K36 704-15K36T

Transient Voltage Suppressor, Unidirectional

FEATURES:

- Equivalent Industry Standard Part Numbers 704-15K36 & 704-15K36T
- Designed For MIL-STD-704
- 28 Volt Power Supply Protection
- Can be supplied with JAN/JANTX parts

This series is primarily for use in avionics equipment. It meets all applicable environmental requirements of MIL-S-19500. These 15kW assemblies are designed typically to operate with a minimum source impedance of .25 Ohms for transients.

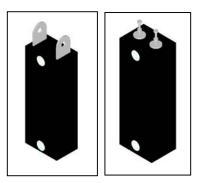
Rating	Condition	Minimum	Maximum	Units	
Peak Pulse Power	@ 25°, 1ms	-	15,000	Watts	
Dissipation					
Steady State Power	-	-	10	Watts	
Dissipation					
t _{clamping}	0 Volts to $V_{(BR)}$	-	< 1x 10 ⁻¹²	Seconds	
Operating & Storage Temp.	-	-65	+ 150	°C	
Forward Surge Current	1/120 sec. @ 25°C	-	300	Amps	
Duty Cycle	-	-	0.01	%	

MAXIMUM RATINGS

ELECTRICAL CHARACTERISTICS @ 25° (Test Both Polarities)

			Minimum			Maximum Forward
Part Number	Reverse Stand-Off	Maximum Reverse	Breakdown	Maximum	Maximum	Voltage
	Voltage	Leakage	Voltage	Clamping Voltage	Peak Pulse Current	V _F
	(Note 1)	$@V_{wm}$	@ 10 mA	@ I _{PP}	(Fig. 2)	@ 8.3 msec.
	V_{WM}	ID	V _(BR)	Vc	I_{PP}	100A
	Volts	μΑ	Volts	Volts	Amps	Volts DC
704-15K36	31.5	100	36	51	300	3.0
704-15K36T	31.5	100	36	51	300	3.0

Note 1: A device is normally selected according to the reverse "Stand Off Voltage" (V_{WM}) which should be equal to or greater than the DC or continuous peak operating voltage level. Special Voltages available from the factory.

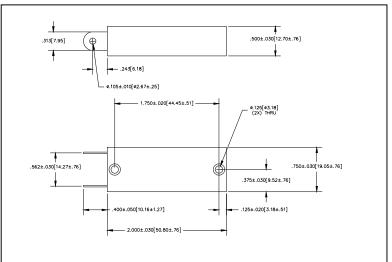


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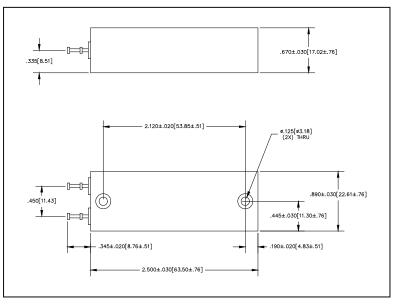
MECHANICAL CHARACTERISTICS

CASE: Molded Case TERMINAL: Silver Plated Brass POLARITY: Cathode terminal marked with a dot WEIGHT: 38 grams MOUNTING POSITION: Any



MECHANICAL DIMENSIONS: In Inches / mm

Flat Leads



Turret Leads

SUBMODULE SCREENING TEST PLAN For Modules H1, H2, and H3

Test	Condition	MIL-STD-750 Test Method
Storage	TA = +175C for 24 hours	1032
Temp Cycle	-65C to +175C, 20 cycles, 15 minutes each extreme	1051
Acceleration	20KG, Y1 axis, no hold time	2006
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
Pulse	20 pulses @ rated lpp tp = 10μS X 1000μS	
Electrical	Reverse Current (IR) @ rated VR	4016
Bum - In	TA = +125C @ rated VR for 96 hours	1038
Electrical	Reverse Current (IR) @ rated VR D-IR = 50% or 1 μ A, whichever is >	4016
	Breakdown voltage (BV) @ IZ D-BV = +-2% from initial reading	4022
Fine Leak	5 X 10-8 atmcc/sec	1071G/H
Gross Leak	T = +125C for 1 min, no bubbles	1071C/D
Group A	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ Clamping voltage (VC) @ Ipp tp = $10\mu S \times 1000\mu S$ Forward voltage (VF) @ IF	4016 4022 4011
·	tp = 8.3 msec	

NOTE: For bidirectional devices test both polarities-split hours on Burn-in test and surge pulses to 50% each polarity.

Attributes Data Supplied Module - H1, H2, H3

MODULE SCREENING TEST PLAN For Module H1

<u>Test</u>

MIL-STD-750 Test Method

4016, 4022

Group A Electricals

Attributes Data Supplied Module - H1

MODULE SCREENING TEST PLAN For Module H2

Test	Condition	MIL-STD-750 Test Method
Storage	TA = +150C for 24 hours	1032
Temp Cycle	-65C to +150C, 10 cycles, 30 minutes each extreme	1051
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
Pulse	20 pulses @ rated lpp tp = rated	
Electrical	Reverse Current (IR) @ rated VR	4016
Burn - In	TA = +125C @ rated VR for 96 hours	1038
Electrical	Reverse Current (IR) @ rated VR D-IR = 50% or 1 μ A, whichever is >	4016
	Breakdown voltage (BV) @ IZ D-BV = +-2% from initial reading	4022
Group A	Reverse Current (IR) @ rated VR	4016
	Breakdown voltage (BV) @ IZ Clamping voltage (VC) @ Ipp tp = rated	4022
	Forward voltage (VF) @ IF tp = 8.3 msec	4011

NOTE: For bidirectional devices test both plarities-split hours on Burn-in test and surge pulses to 50% each polarity.

Attributes Data Supplied Module - H2

MODULE GROUP B TESTING For Module H3

Test	Condition	MIL-STD-750 Test Method
SUBGROUP 1:) I	
Solderability Resistance to solvents		2026 1022
SUBGROUP 2:		
Temp Cycling	-65C/+150C, 10 cycles, 30 minutes each extreme	1051
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
SUBGROUP 3:		
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
Operating Life	@ rated VR, TA = +125C for 340 hours	1026
Electrical	Reverse Current (IR) @ rated VR D-IR = 50% or 1 μ A, whichever is >	4016
	Breakdown voltage (BV) @ IZ D-BV = +-5% from initial	4022

NOTE: For bidirectional devices test both polarities-split hours on Operating Life to 50% each polarity.

Attributes Data Supplied Sampling per MIL-S-19500 Module - H3 (Group B)

MODULE GROUP C TESTING For Module H3

Test	Condition	MIL-STD-750 Test Method
SUBGROUP 1:		
Physical dimensions	1. 1. 1. 1. 1.	2066
SUBGROUP 2:		
Terminal strength (tension)	Test condition A, W = 10lbs., t = 15 seconds	2036
Moisture resistance	Omit inital conditioning	1021
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
SUBGROUP 3:		
Shock	1500G's, 0.5ms, 5 blows in each orientation X1, Y1, Z1	2016
Vibration, var. freq.		2056
Electrical	Reverse Current (IR) @ rated VR Breakdown voltage (BV) @ IZ	4016 4022
SUBGROUP 4:		
Salt atmosphere		1041
SUBGROUP 5:		
Operating Life	@ rated VR, TA = +125C for 1000 hours	1026
Electrical	Reverse Current (IR) @ rated VR D-IR = 50% or 1 μ A, whichever is >	4016
	Breakdown voltage (BV) @ IZ D-BV = +-5% from initial	4022

NOTE: For bidirectional devices test both polarities-split hours on Operating Life to 50% each polarity.

Attributes Data Supplied Sampling per MIL-S-19500 Module - H3 (Group C)



TECHNICAL DATA

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